- 1. 準備: GDS 檔
- 2. 複製 DRC 檔案,可使用如下指令:
 - [1] Calibre: cp-R/cad/CBDK/CBDK IC Contest v2.5/Calibre/drc.
 - [2] IC Validator: cp -R /cad/CBDK/CBDK_IC_Contest_v2.5/icv/drc.
- 3. 修改 DRC 檔案,請先進入 drc 資料夾
 - [1] Calibre:
 - i. 開啟文檔 CL13S 8M.22d
 - ii. 註解第 23 行的#DEFINE FULL CHIP
 - iii. 修改第 169 行的雙引號內容,改為自己的 GDS 路徑
 - iv. 修改第 170 行的雙引號內容,改為自己的 TOP MODULE 名稱

```
//#DEFINE 2.5V // When HIGH_VOI
//#DEFINE 1.8V // when HIGH_VOI
//#DEFINE FULL_CHIP // V
//#DEFINE BIGSeatringCorner
L68 LAYOUT SYSTEM GDSII
L69 LAYOUT PATH "../ISE apr.gds"
L70 LAYOUT PRIMARY "ISE"
```

[2] IC Validator

- i. 開啟文檔 run icv drc
- ii. 修改第 4 行的雙引號內容,改為自己的 GDS 路徑
- iii. 修改第7行的雙引號內容,改為自己的TOP MODULE名稱

- 4. 執行 DRC,使用如下指令:
 - [1] Calibre: calibre-drc-hier CL13S 8M.22d
 - [2] IC Validator: ./run icv drc

5. 確認結果

[1] Calibre: 看畫面中的 TOTAL RESULTS GENERATED 是否為 0

```
Cumulative INSIDE/EXTENT CELL Time: CPU = 0 REAL = 0
Cumulative POLYGON TOPOLOGICAL Time: CPU = 0 REAL = 0
Cumulative POLYGON MEASUREMENT Time: CPU = 0 REAL = 0
Cumulative HOLES Time: CPU = 0 REAL = 0
Cumulative STARE Time: CPU = 1 REAL = 1
Cumulative EDGE TOPOLOGICAL Time: CPU = 0 REAL = 0
Cumulative EDGE TOPOLOGICAL Time: CPU = 0 REAL = 0
Cumulative STAMP Time: CPU = 0 REAL = 0
Cumulative STAMP Time: CPU = 0 REAL = 0
Cumulative ONE-LAYER DRC Time: CPU = 1 REAL = 1
Cumulative ONE-LAYER DRC Time: CPU = 1 REAL = 1
Cumulative ONE-LAYER DRC Time: CPU = 0 REAL = 0
Cumulative TWO-LAYER DRC Time: CPU = 0 REAL = 0
Cumulative NET AREA (RATIO) Time: CPU = 0 REAL = 0
Cumulative NET AREA (RATIO) Time: CPU = 0 REAL = 0
Cumulative SHIFT/GROW/SHRINK Time: CPU = 0 REAL = 0
Cumulative SHIFT/GROW/SHRINK Time: CPU = 0 REAL = 0
Cumulative WITH EDGE Time: CPU = 0 REAL = 0
Cumulative WITH EDGE Time: CPU = 0 REAL = 0
Cumulative MITH EDGE TIME: CPU = 0 REAL = 0
Cumulative MITH EDGE TIME: CPU = 0 REAL = 0
Cumulative MITH EDGE TIME: CPU = 0 REAL = 0
Cumulative ROB Time: CPU = 0 REAL = 0

Cumulative ROB Time: CPU = 0 REAL = 0

Cumulative ROB Time: CPU = 0 REAL = 0

Cumulative ROB Time: CPU = 0 REAL = 0

--- CALIBRE::DRC-H EXECUTIVE MODULE COMPLETED. CPU TIME = 21 REAL TIME = 22

--- TOTAL CPU TIME = 21 REAL TIME = 22

--- PROCESSOR COUNT = 1

--- SUMMARY REPORT FILE = DRC.rep

[alex@tiffany apr/drc]$
```

[2] IC Validator: 開啟文檔"某某.LAYOUT_ERRORS",某某為 TOP MODULE 名稱,只要最上面是 CLEAN 即可

```
LAYOUT ERRORS RESULTS: CLEAN
                 #### #
                           #####
                                   ##
                                       ## #
                                 ###### # # #
                      #
                 #### ##### ##### #
                                      # #
 ______
Library name: ../ISE_apr.gds
Structure name: ISE
Generated by: IC Validator RHEL64 R-2020.09-SP3-3.6450417 2021/04/23
               ICV13S_8M.drc.rs
Runset name:
<mark>J</mark>ser name:
               alex
                2023/04/21 05:31:18PM
Time started:
               2023/04/21 05:31:45PM
Time ended:
Called as: icv -vue -i ../ISE_apr.gds -c ISE -host_init 1 -host_login ssh ICV:
                      ERROR SUMMARY
BJT.R.1 : RPO needs to cover 0.3 on EM OD edge from
OD and STI sides
                                         ..... 0 violations found.
CDU.R.1 : CDUDMY must be inside the assembly
isolation, beside the seal ring.
  copy ..... 0 violations found.
```

6. 看有哪些錯

- [1] Calibre: calibre-rve DRC RES.db
- [2] IC Validator: 開啟文檔"某某.LAYOUT_ERRORS",某某為 TOP MODULE 名稱,查看問題